

SOT-89 Plastic-Encapsulate Transistors

FEATURES

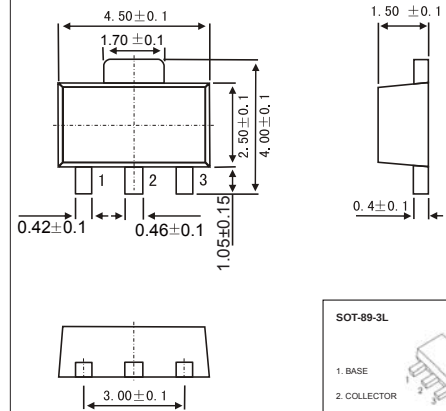
- High Breakdown Voltage
- TRANSISTOR (PNP)

MECHANICAL DATA

- Case style:SOT-89 -3L molded plastic
- Mounting position:any

SOT-89-3L

Unit:mm



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-400	V
V_{CEO}	Collector-Emitter Voltage	-400	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-0.2	A
I_{CM}	Collector Current- Pulsed	-0.3	A
P_C	Collector Power Dissipation	0.5	W
T_J	Junction Temperature	150	°C
T_{stg}	storage Temperature	-55~+150	°C

PACKAGE INFORMATION

Device	Package	Shipping
A94	SOT-89	1000/Tape&Reel

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR) CBO}$	$I_C = -100\mu A, I_E = 0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR) CEO}$	$I_C = -1mA, I_B = 0$	-400			V
Emitter-base breakdown voltage	$V_{(BR) EBO}$	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -400V, I_E = 0$			-0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE} = -400V, I_B = 0$			-5	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -10V, I_C = -10mA$	80		300	
	$h_{FE(2)}$	$V_{CE} = -10V, I_C = -1mA$	70			
	$h_{FE(3)}$	$V_{CE} = -10V, I_C = -100mA$	60			
	$h_{FE(4)}$	$V_{CE} = -10V, I_C = -50mA$	80			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.2	V
	$V_{CE(sat)}$	$I_C = -50mA, I_B = -5mA$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -10mA, I_B = -1mA$			-0.75	V
Transition frequency	f_T	$V_{CE} = -20V, I_C = -10mA$ $f = 30MHz$	50			MHz

Marking

Marking	A94
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RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics

